

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
12 May 2005 (12.05.2005)

PCT

(10) International Publication Number
WO 2005/043605 A1

(51) International Patent Classification⁷: **H01L 21/02**,
27/06, 27/01

(21) International Application Number:
PCT/IB2004/052085

(22) International Filing Date: 14 October 2004 (14.10.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
03104002.5 29 October 2003 (29.10.2003) EP

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

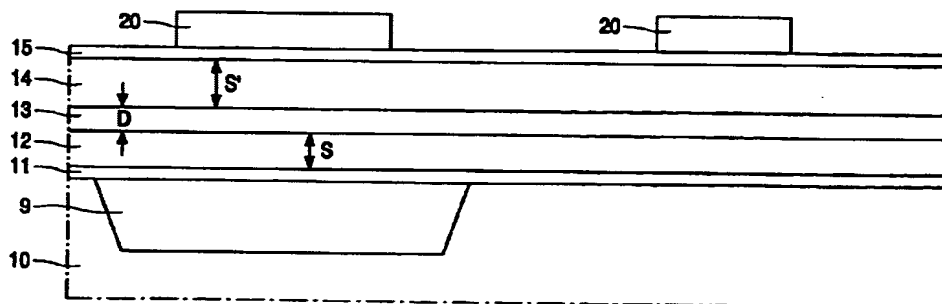
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,
SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:

— as to applicant's entitlement to apply for and be granted
a patent (Rule 4.17(ii)) for the following designations AE,
AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ,
CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE,
EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS,

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(54) Title: INTEGRATED CIRCUIT WITH PARTLY SILICIDATED SILICON LAYER



(57) Abstract: The integrated circuit (1) comprises an electric device (2) such as a resistor which comprises a first silicon layer (120) having a silicidated part (122) and a non-silicidated part (123), and a further electric device (3) such as, e.g. a capacitor, a field effect transistor or a non-volatile memory gate stack. The further electric device (3) comprises a dielectric layer (130) having a dielectric layer thickness (D). The non-silicidated part (123) of the electric device (2) is covered by a further dielectric layer (131) having the dielectric layer thickness (D), the silicidated part (122) is not covered by the further dielectric layer (131). Such an integrated circuit (1) may be formed by a method according to invention which involves a reduced number of lithography steps.